

FIG.1

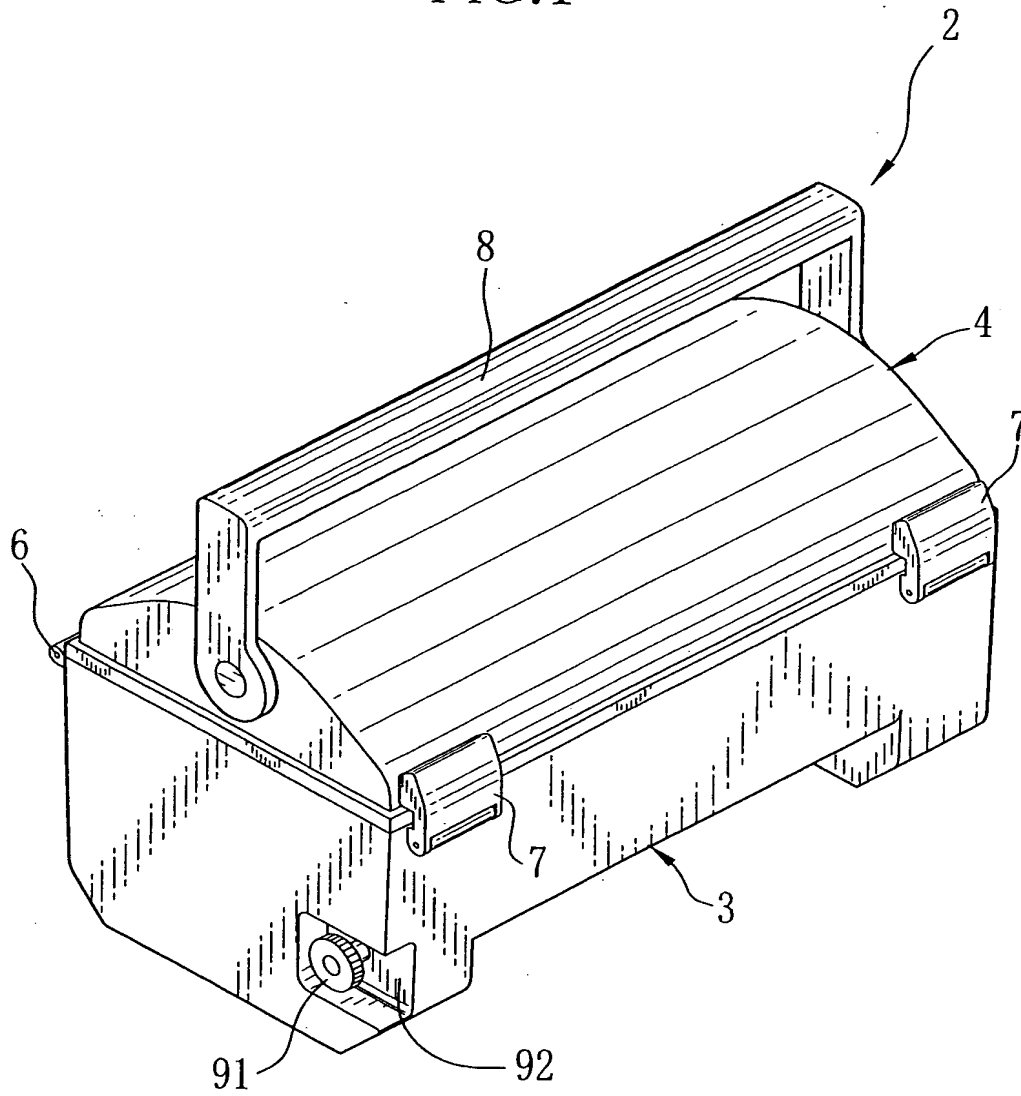


FIG.2

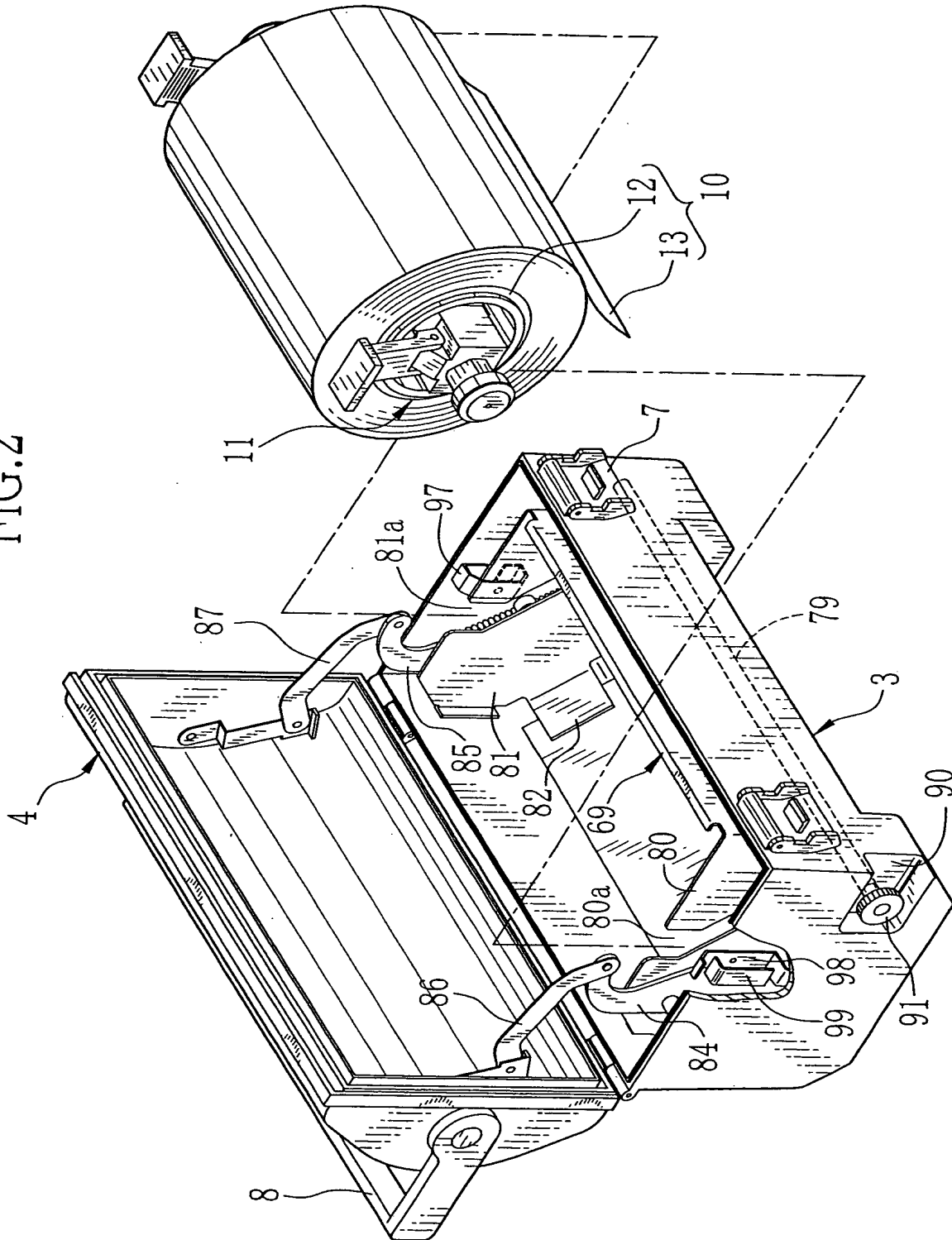


FIG.3

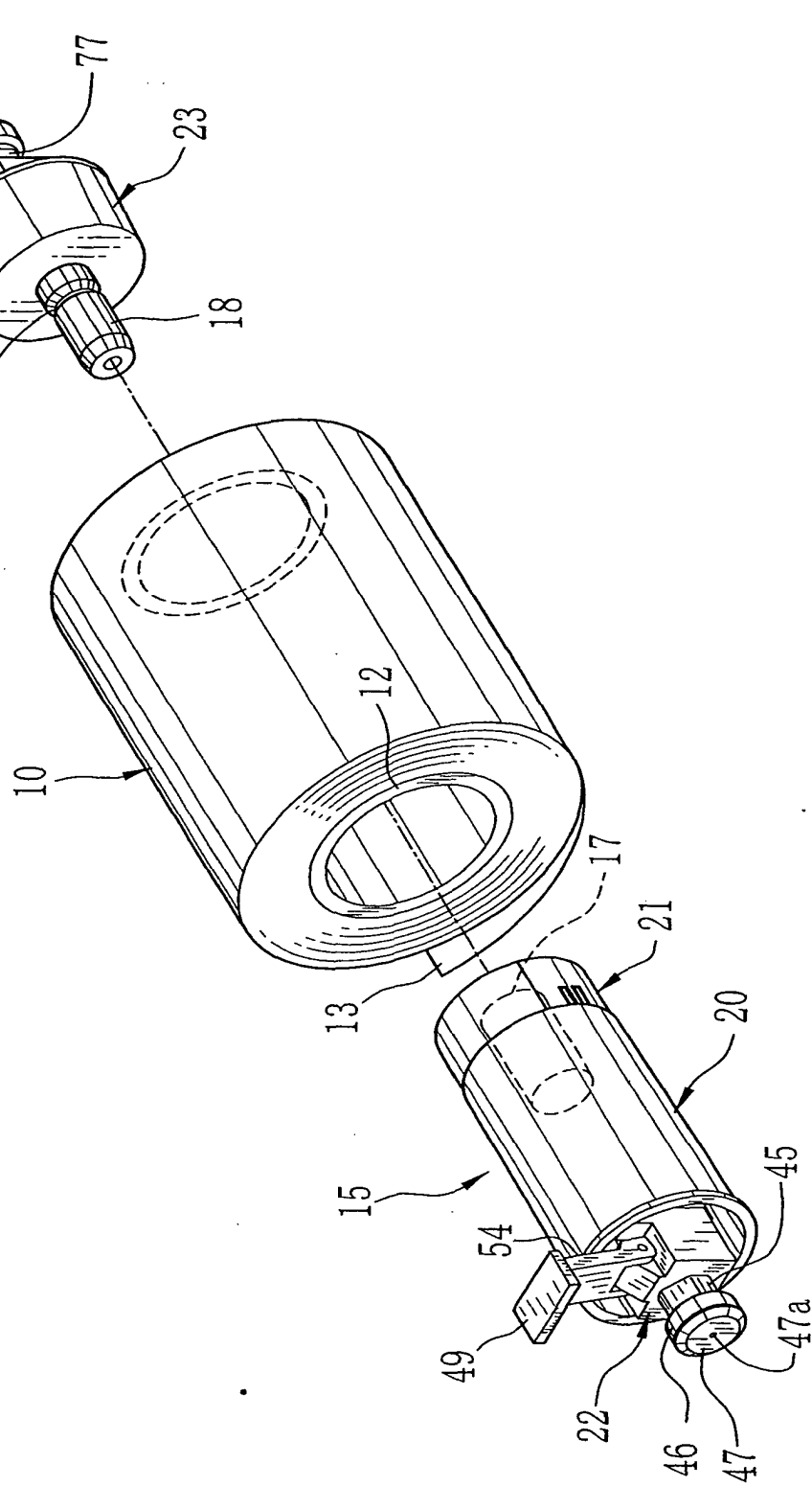
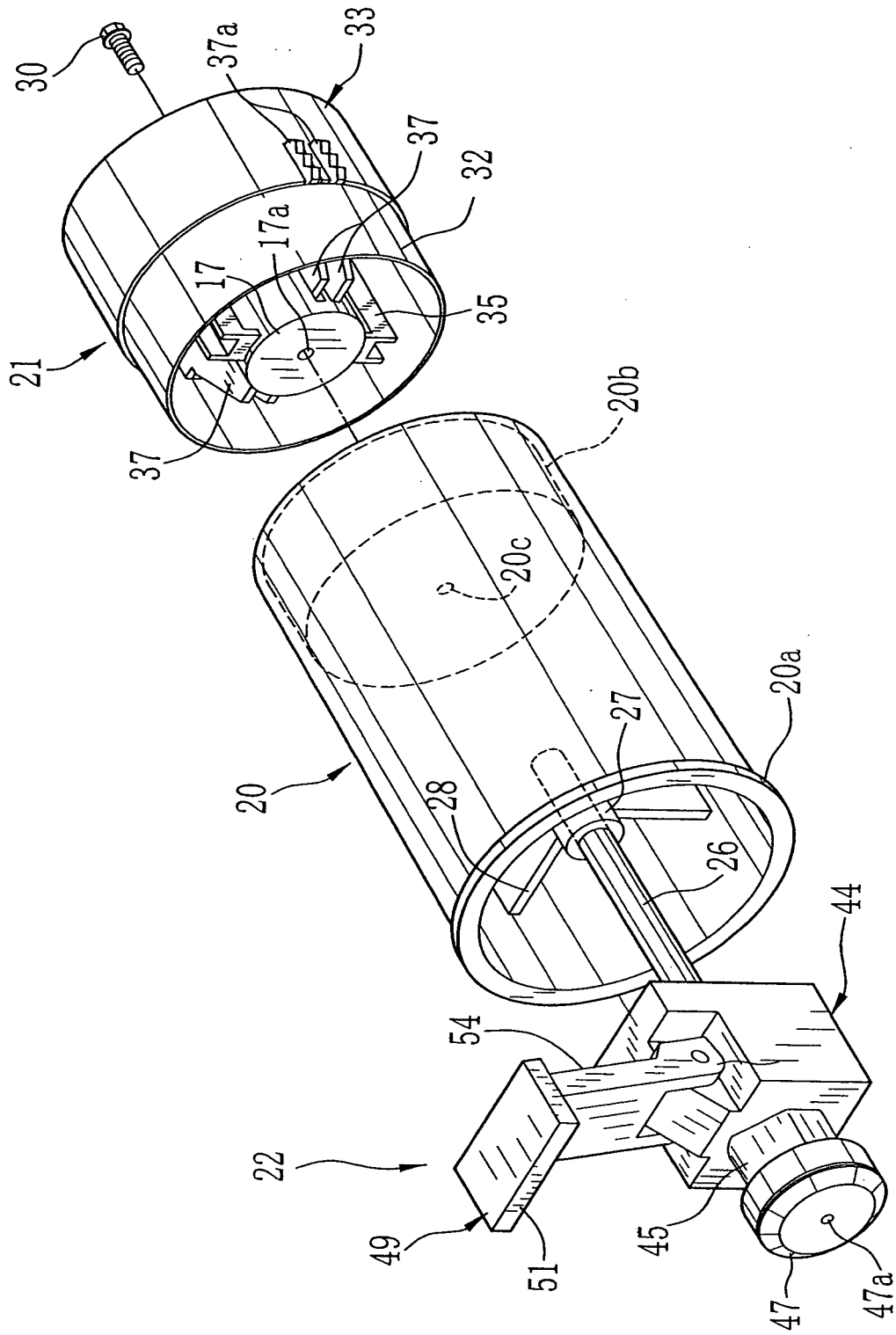


FIG.4



4

FIG. 6

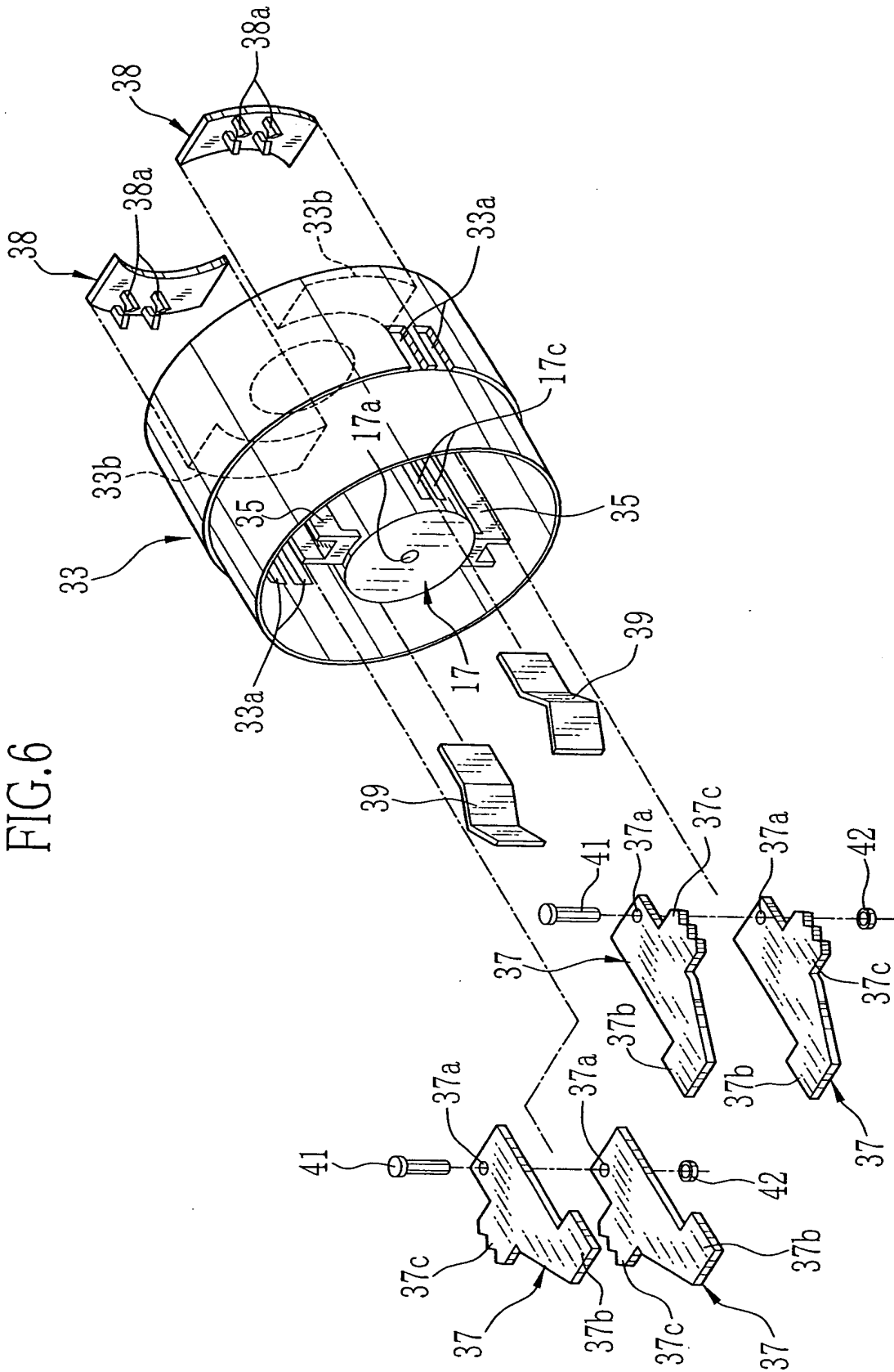


FIG. 7

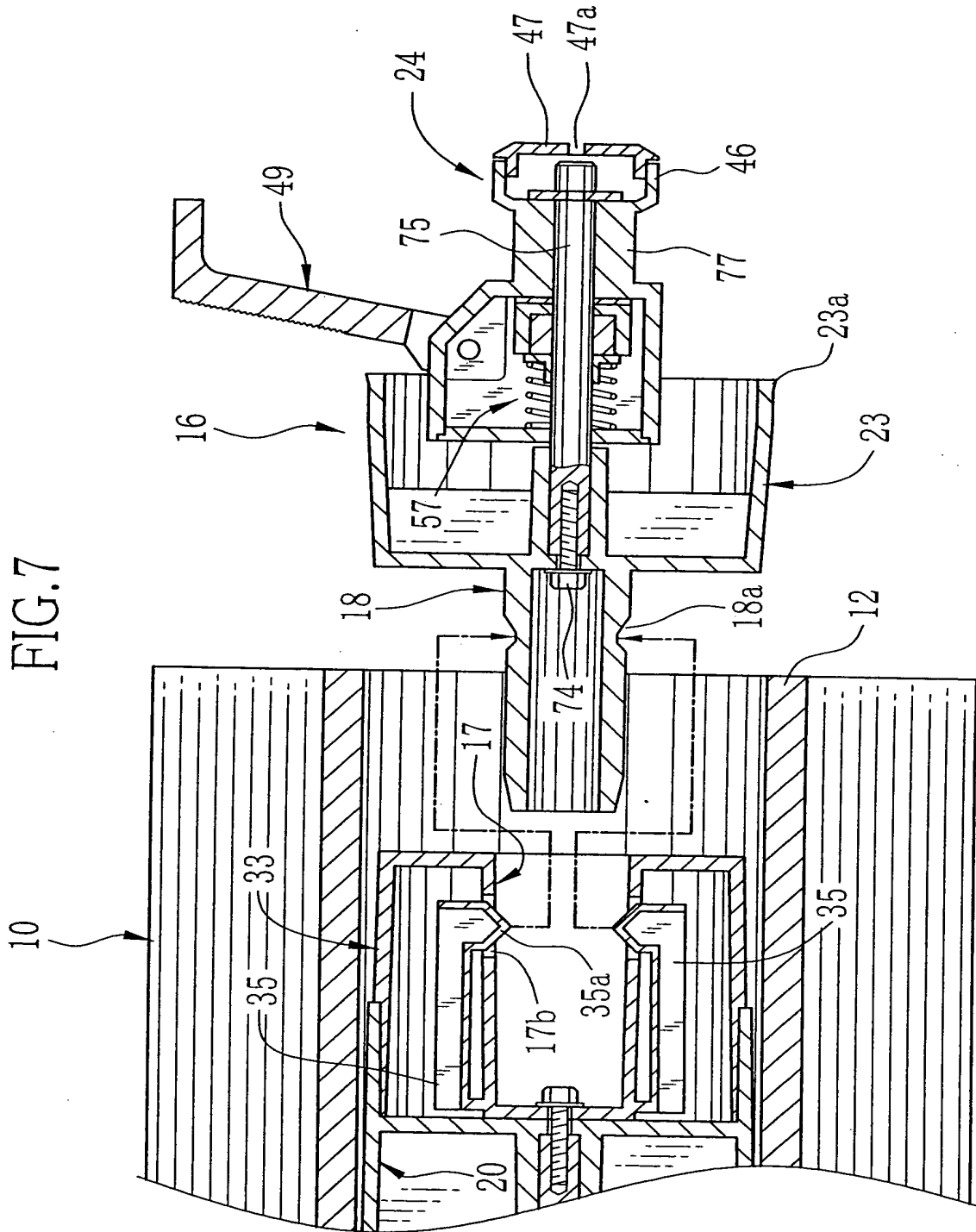


FIG. 8

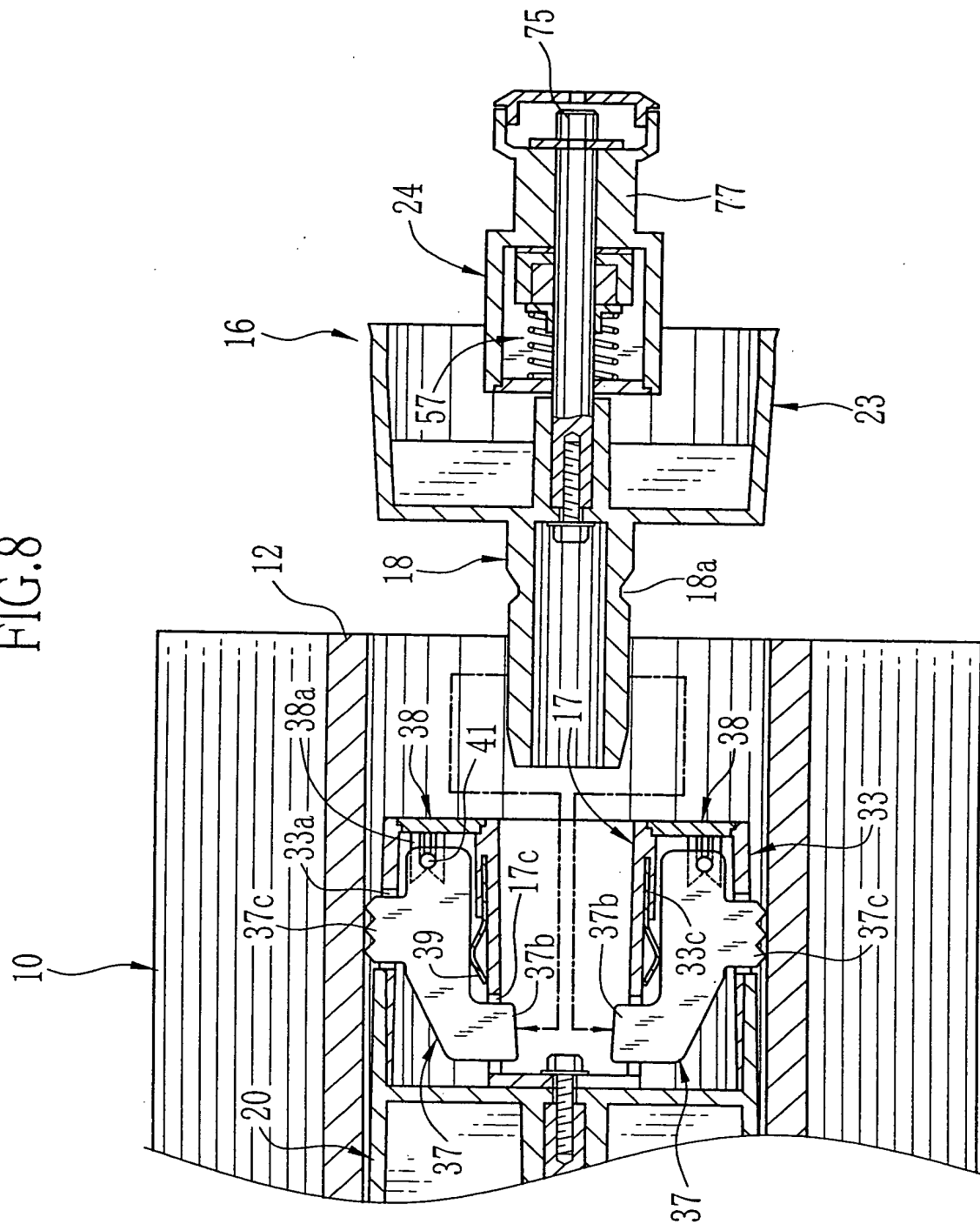
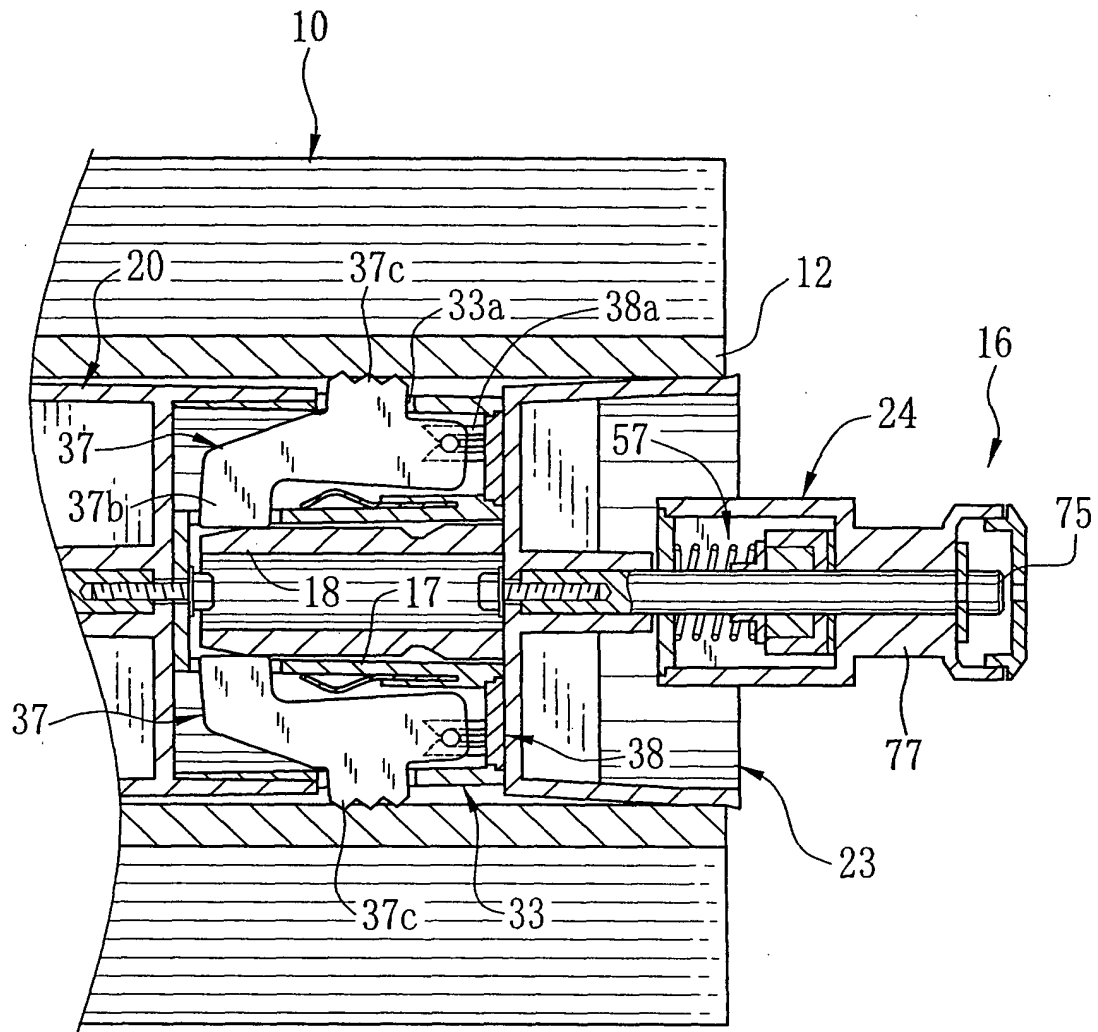




FIG.9



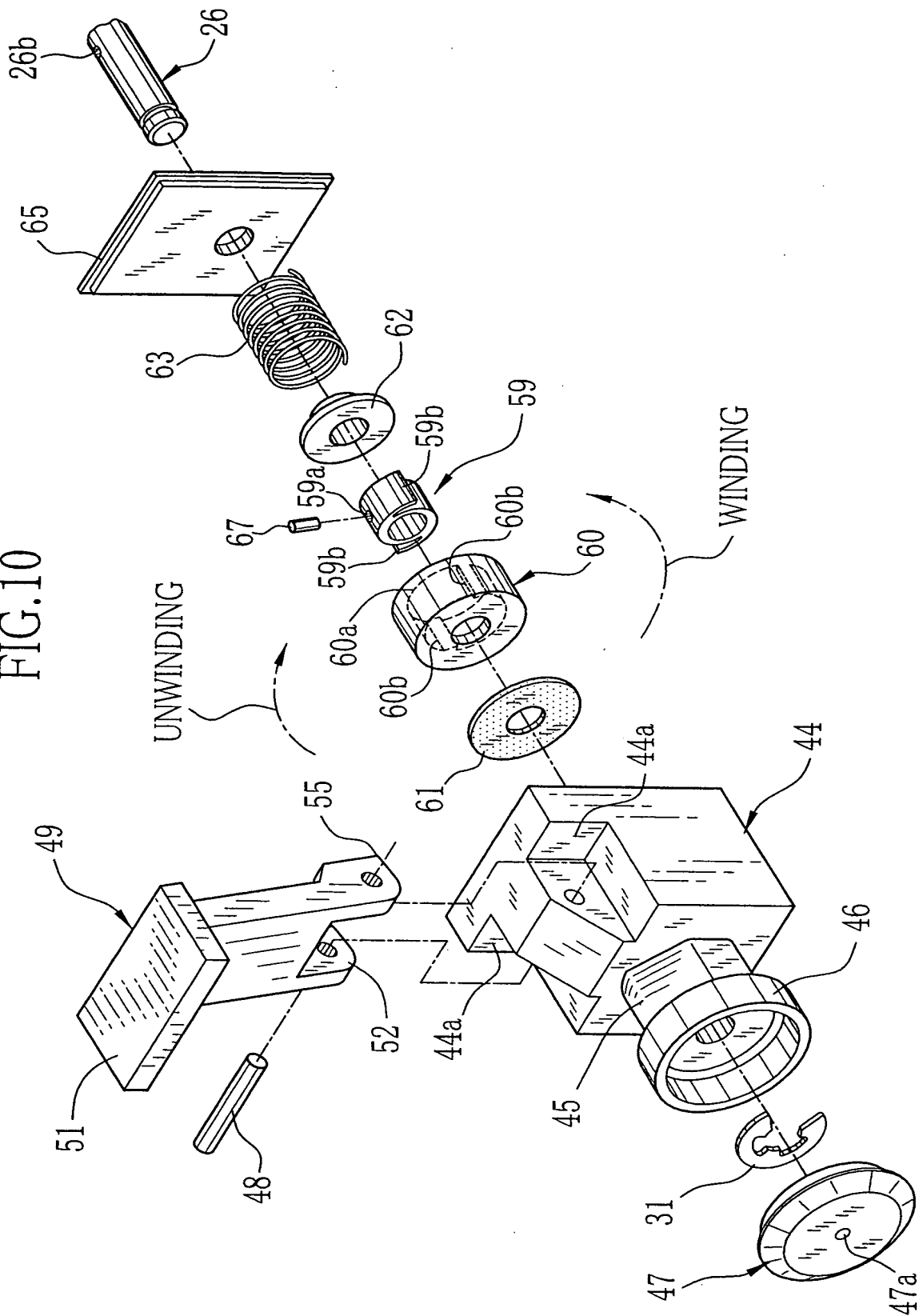
[illegible]

FIG.11

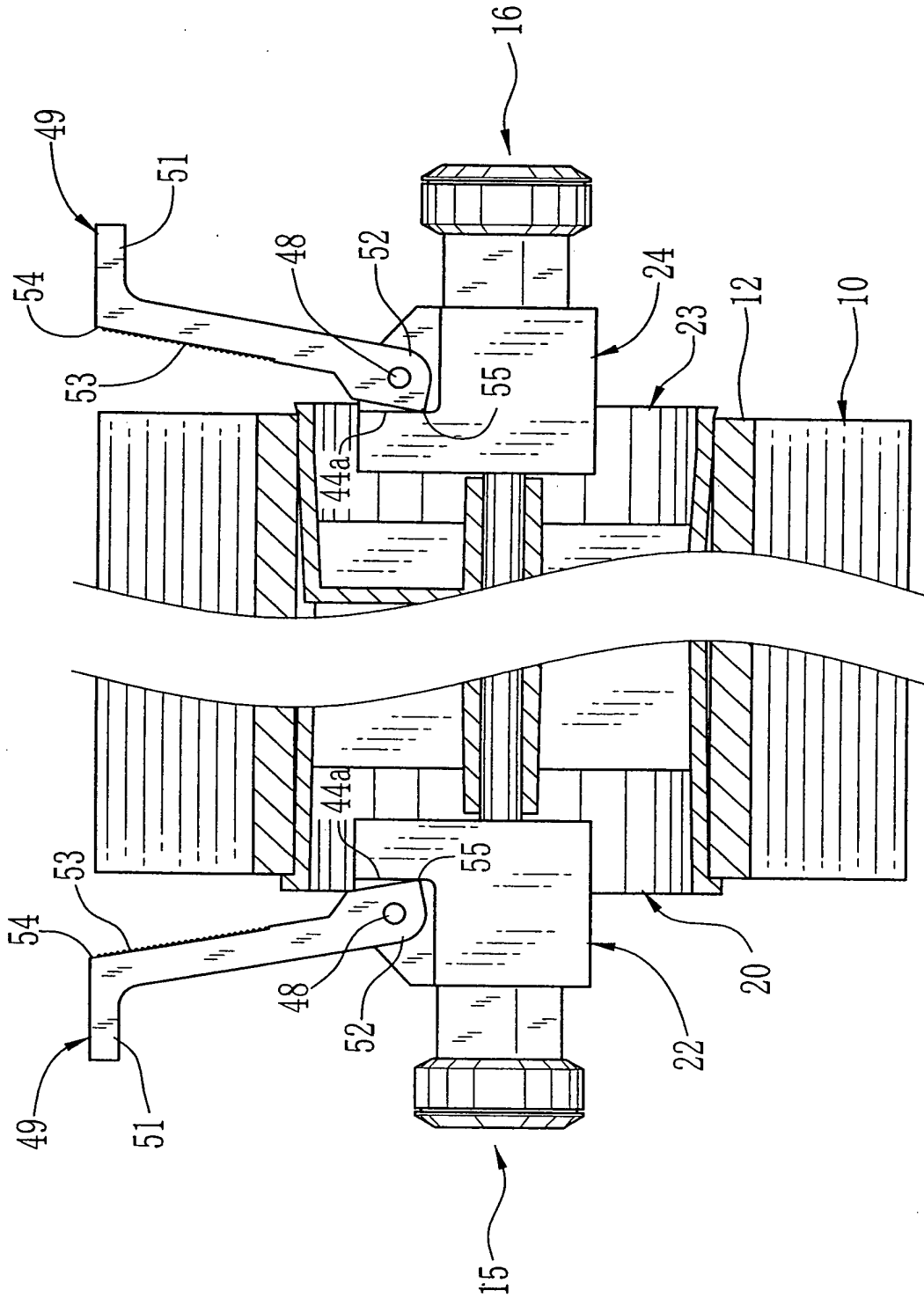


FIG.12

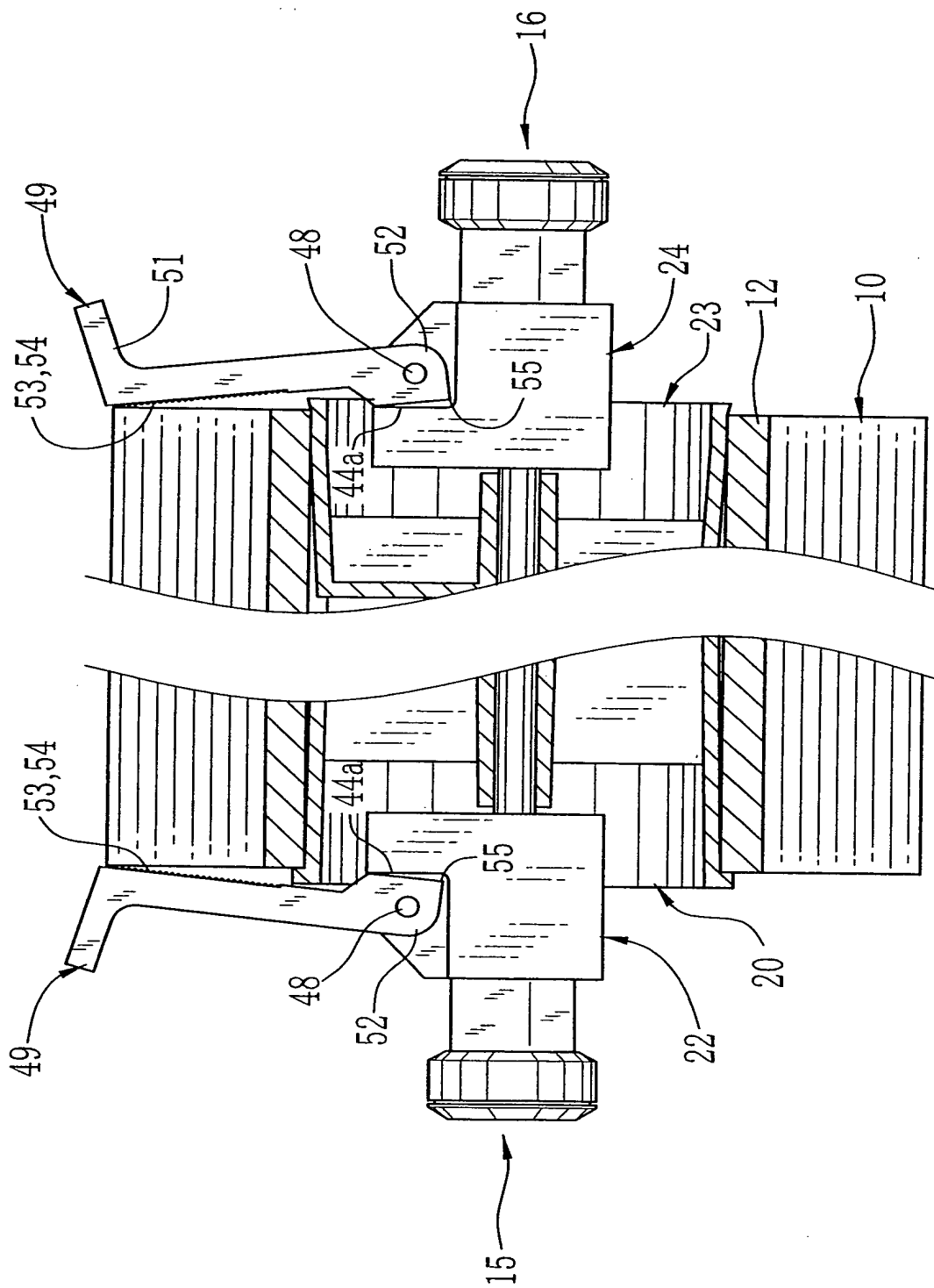


FIG.13A

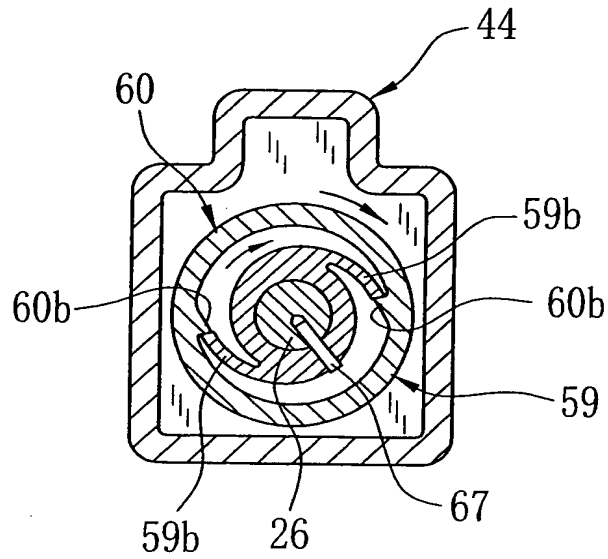


FIG.13B

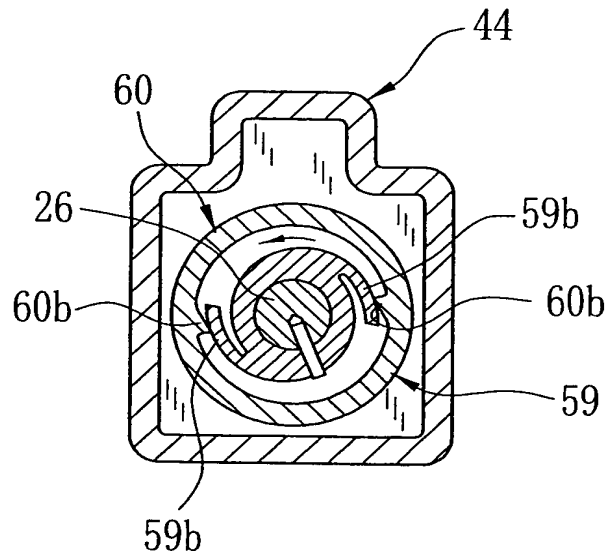


FIG.14

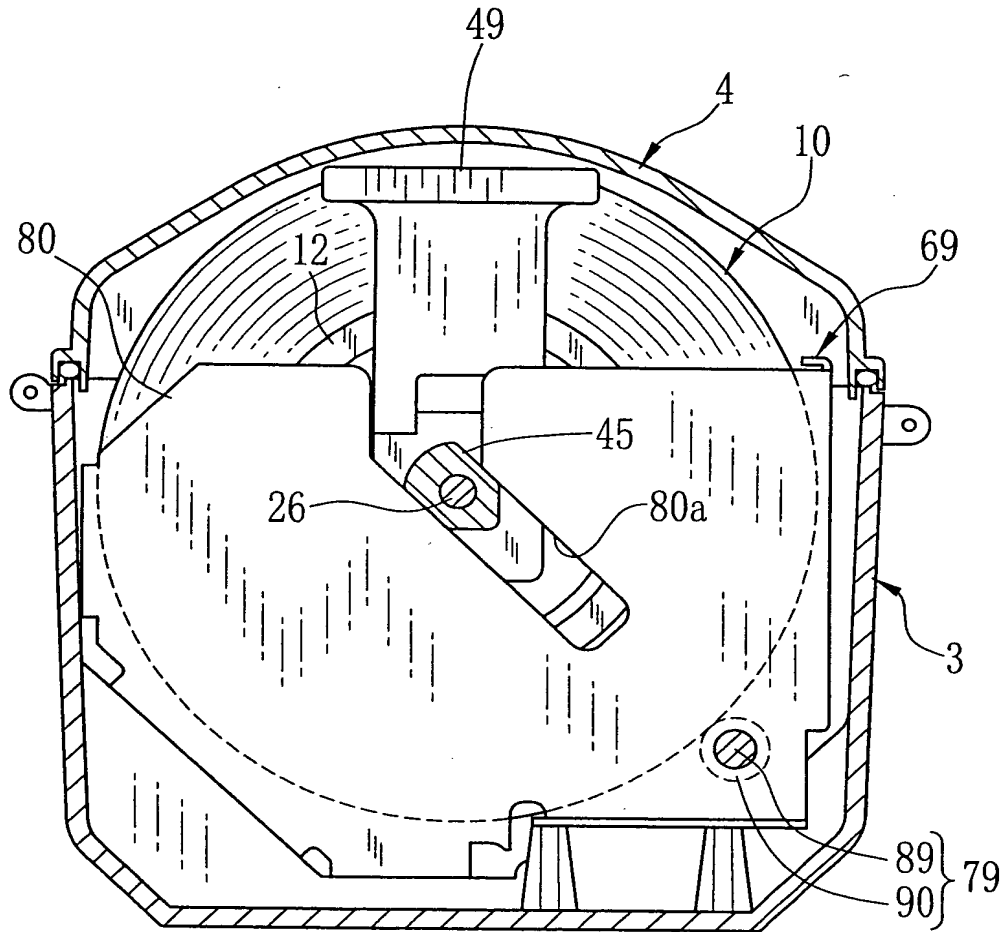


FIG.15

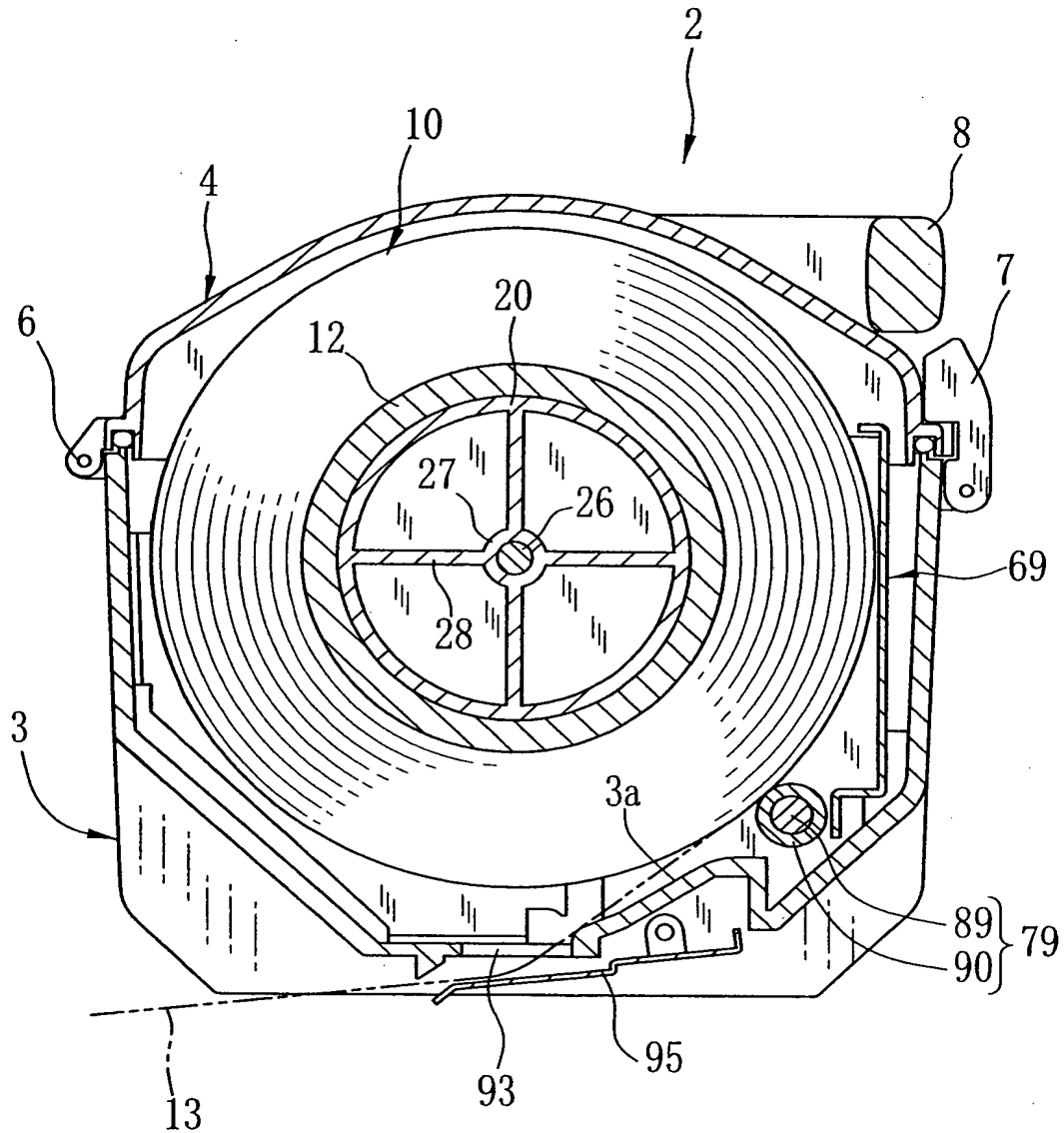


FIG.16

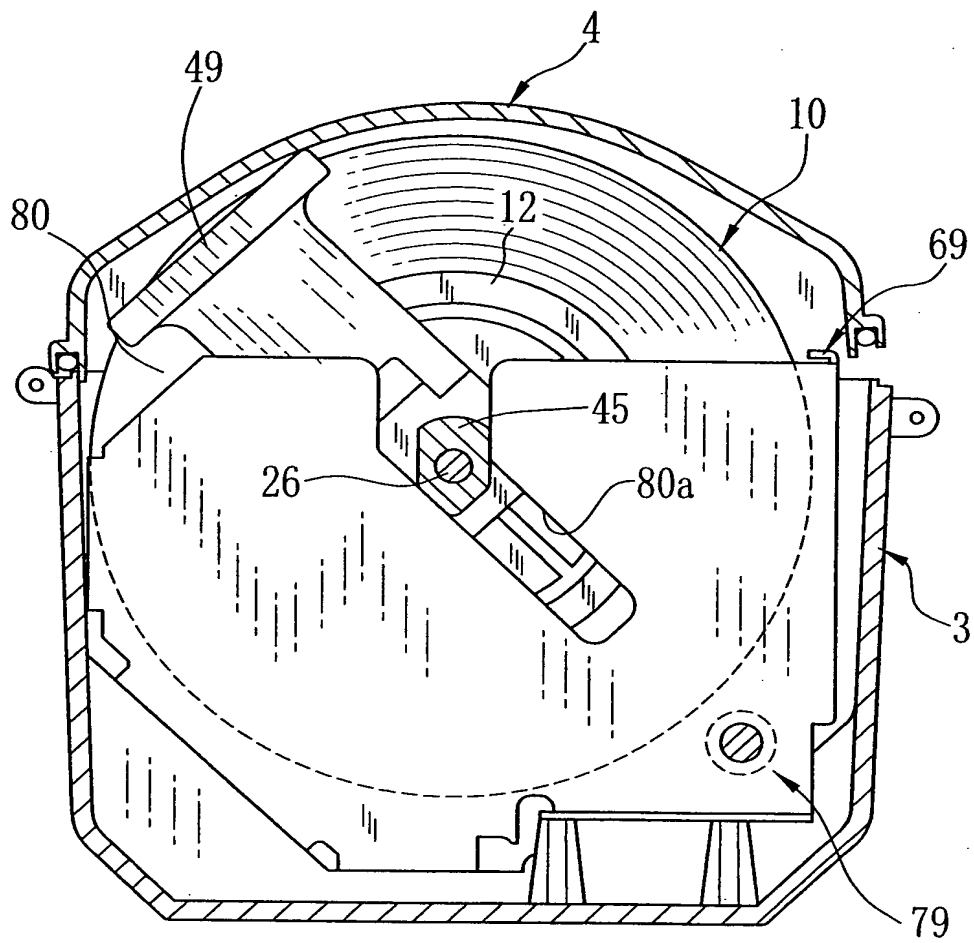




FIG.17

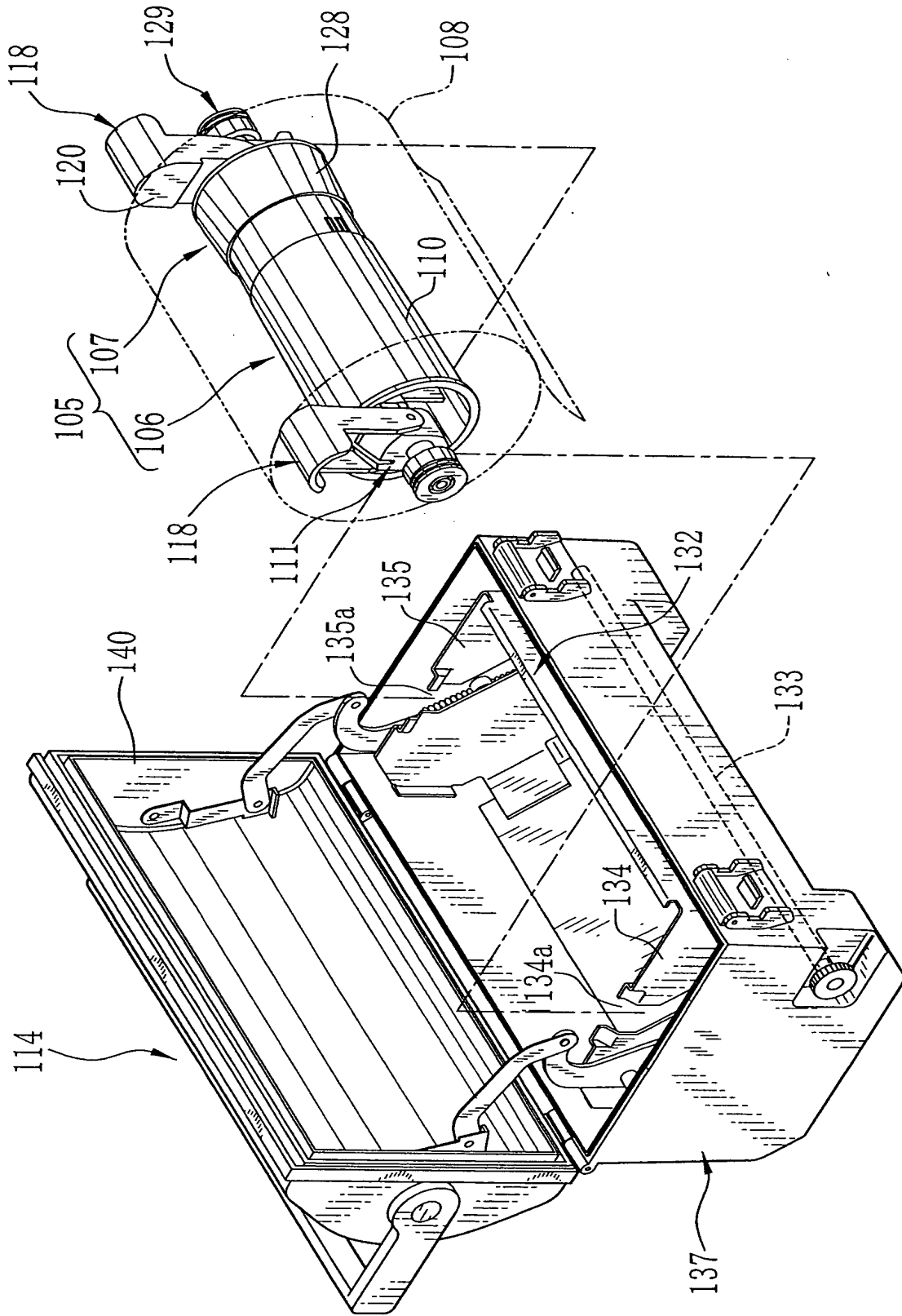


FIG. 1 is a cross-sectional view of a semiconductor device. The device includes a substrate 108 with a top layer 118. A central region 110 contains a structure 112. A side region 109 contains a structure 128. A bottom layer 120 is shown. Various other components are labeled with reference numerals: 111, 113, 115, 116, 117, 125, 126, 129, 130, 134, 134a, 135, 135a, 137.

FIG. 18

FIG. 19

